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## Silicon NPN Power Transistor

## 2SC2706

### DESCRIPTION

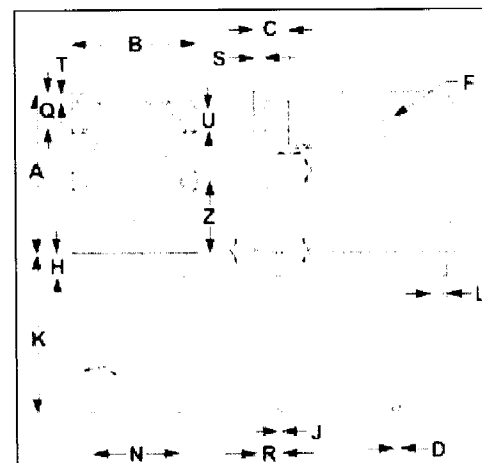
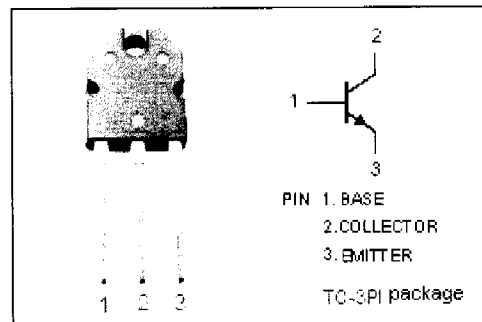
- Collector-Emitter Breakdown Voltage:  
:  $V_{(BR)CEO} = 140V(\text{Min})$
- Complement to Type 2SA1146

### APPLICATIONS

- Audio frequency low power amplifier applications
- Recommend for 70W audio frequency amplifier output stage applications

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	140	V
$V_{CEO}$	Collector-Emitter Voltage	140	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	10	A
$I_B$	Base Current-Continuous	1	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

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**Silicon NPN Power Transistor****2SC2706****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	140			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=5\text{A}; V_{CE}=5\text{V}$			2.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=140\text{V}; I_E=0$			50	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			50	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	55		240	
$h_{FE-2}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=5\text{V}$	30			
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		130		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=10\text{V}$	25			MHz

◆  **$h_{FE-1}$  Classifications**

R	O	Y
55-110	80-160	120-240